



STB21NM60ND, STF21NM60ND, STP21NM60ND, STW21NM60ND

N-channel 600 V, 0.17 Ω typ., 17 A FDmesh™ II Power MOSFET
in D²PAK, TO-220FP, TO-220 and TO-247 packages

Datasheet — production data

Features

Order codes	V _{DSS} @ T _J max	R _{DS(on)} max	I _D
STB21NM60ND	650 V	< 0.22 Ω	17 A
STF21NM60ND	650 V	< 0.22 Ω	17 A
STP21NM60ND	650 V	< 0.22 Ω	17 A
STW21NM60ND	650 V	< 0.22 Ω	17 A

- Intrinsic fast-recovery body diode
- Worldwide best R_{DS(on)}*area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities

Applications

- Switching applications

Description

These FDmesh™ II Power MOSFETs with intrinsic fast-recovery body diode are produced using the second generation of MDmesh™ technology. Utilizing a new strip-layout vertical structure, these revolutionary devices feature extremely low on-resistance and superior switching performance. They are ideal for bridge topologies and ZVS phase-shift converters.

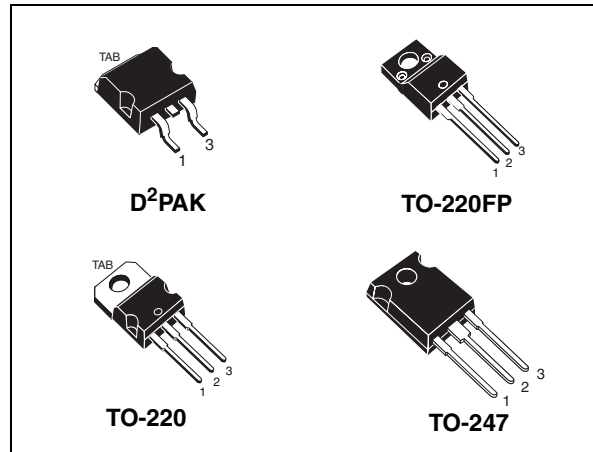
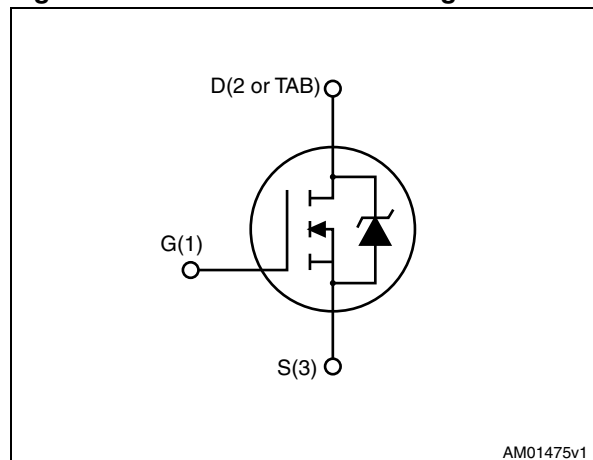


Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB21NM60ND	21NM60ND	D ² PAK	Tape and reel
STF21NM60ND	21NM60ND	TO-220FP	Tube
STP21NM60ND	21NM60ND	TO-220	Tube
STW21NM60ND	21NM60ND	TO-247	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	9
4	Package mechanical data	10
5	Packing mechanical data	18
6	Revision history	20

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, D ² PAK TO-247	TO-220FP	
V _{DS}	Drain-source voltage	600		V
V _{GS}	Gate- source voltage	±25		V
I _D	Drain current (continuous) at T _C = 25 °C	17	17 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	10	10 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	68	68 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	140	30	W
dv/dt ⁽³⁾	Peak diode recovery voltage slope	40		V/ns
V _{iso}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)		2500	V
T _{stg}	Storage temperature	- 55 to 150		°C
T _J	Max. operating junction temperature	150		

- Limited by maximum junction temperature
- Pulse width limited by safe operating area
- I_{SD} ≤ 17 A, di/dt ≤ 600 A/μs, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		D ² PAK	TO-220FP	TO-220	TO-247	
R _{thj-case}	Thermal resistance junction-case max	0.89	4.17	0.89		°C/W
R _{thj-amb}	Thermal resistance junction-ambient max		62.5		50	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max)	8.5	A
E _{AS}	Single pulse avalanche energy (starting T _J = 25 °C, I _D = I _{AS} , V _{DD} = 50 V)	610	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain source voltage slope	$V_{DD} = 480 \text{ V}, I_D = 17 \text{ A}, V_{GS} = 10 \text{ V}$	48			V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600 \text{ V}$ $V_{DS} = 600 \text{ V}, T_C = 125^{\circ}\text{C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10 \text{ V}, I_D = 8.5 \text{ A}$		0.170	0.220	Ω

1. Characteristic value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$	-	1800 90 8	-	pF pF pF
$C_{oss \text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0 \text{ to } 480 \text{ V}$	-	300	-	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 300 \text{ V}, I_D = 8.5 \text{ A}$ $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ <i>(see Figure 23),</i> <i>(see Figure 18)</i>	-	18 16 70 48	-	ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480 \text{ V}, I_D = 17 \text{ A}, V_{GS} = 10 \text{ V},$ <i>(see Figure 19)</i>	-	60 10 30	-	nC nC nC
R_G	Gate input resistance	$f = 1 \text{ MHz}$ Gate DC Bias=0 Test signal level=20 mV Open drain	-	3	-	Ω

1. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				17	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				68	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 17\text{ A}, V_{GS} = 0$			1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 17\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ <i>(see Figure 20)</i>		150		ns
Q_{rr}	Reverse recovery charge			0.90		μC
I_{RRM}	Reverse recovery current			13		A
t_{rr}	Reverse recovery time	$I_{SD} = 17\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 150\text{ }^\circ\text{C}$ <i>(see Figure 20)</i>		210		ns
Q_{rr}	Reverse recovery charge			1.6		μC
I_{RRM}	Reverse recovery current			15		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

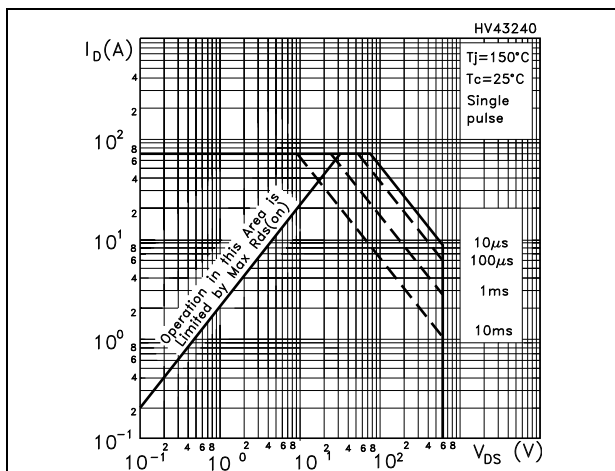


Figure 3. Thermal impedance for TO-220, D²PAK

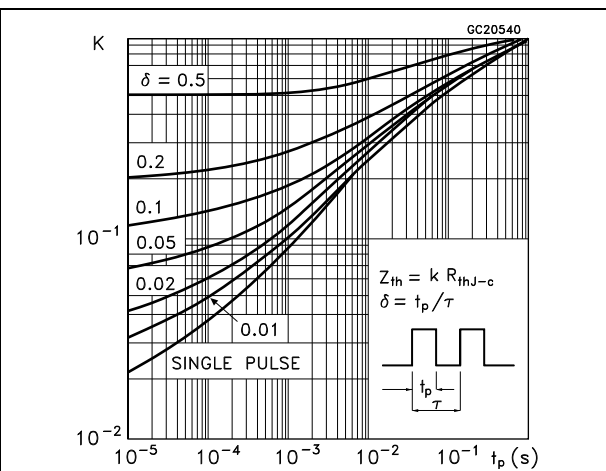


Figure 4. Safe operating area for TO-220FP

Figure 5. Thermal impedance for TO-220FP

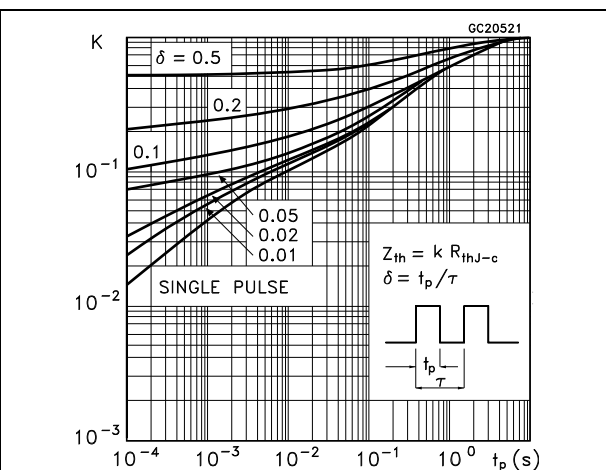
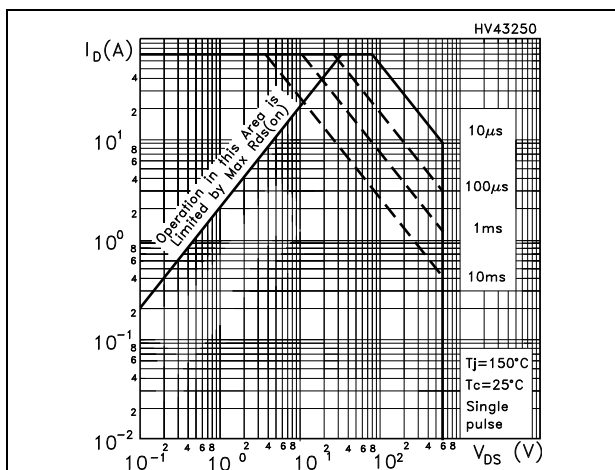


Figure 6. Safe operating area for TO-247

Figure 7. Thermal impedance for TO-247

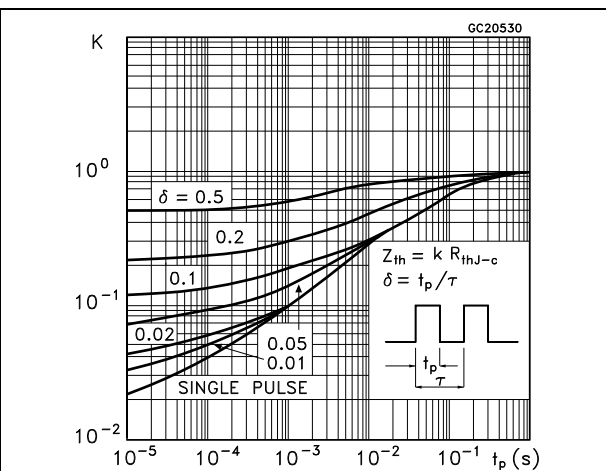
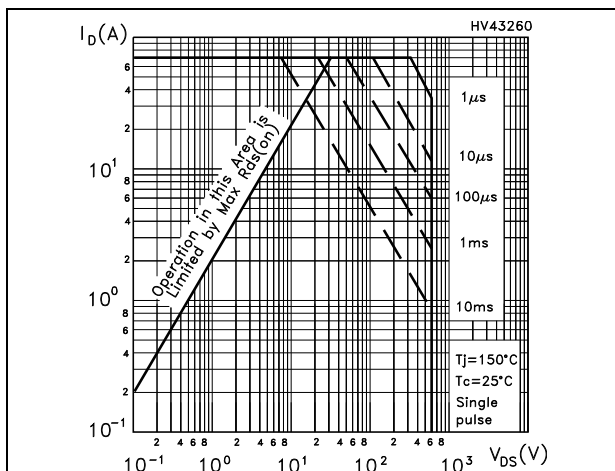


Figure 8. Output characteristics

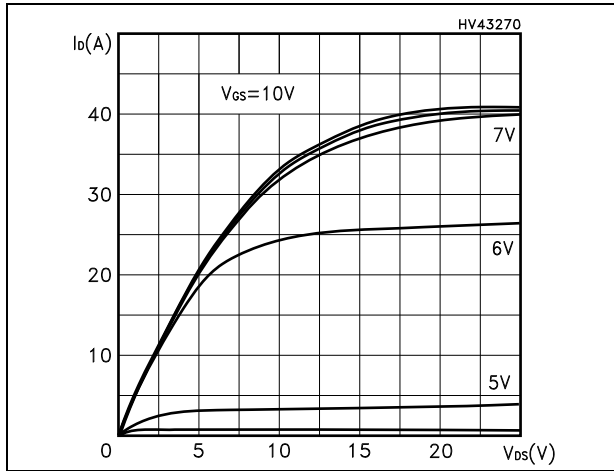


Figure 9. Transfer characteristics

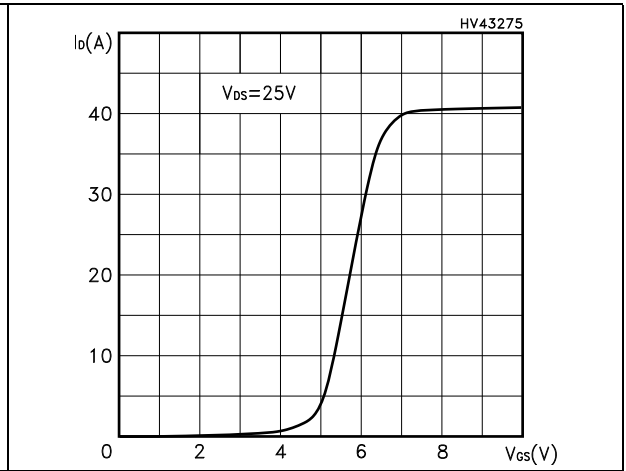


Figure 10. Transconductance

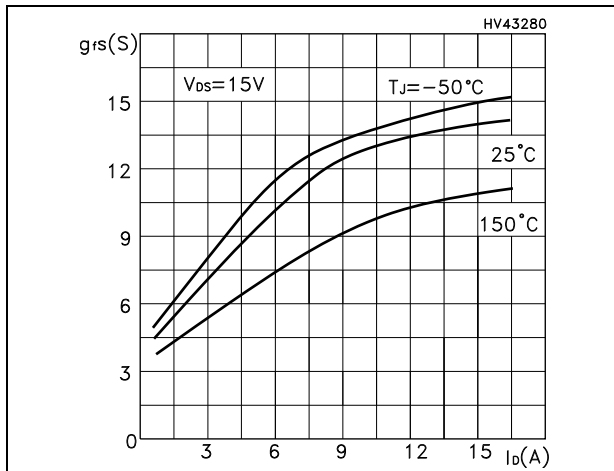


Figure 11. Static drain-source on-resistance

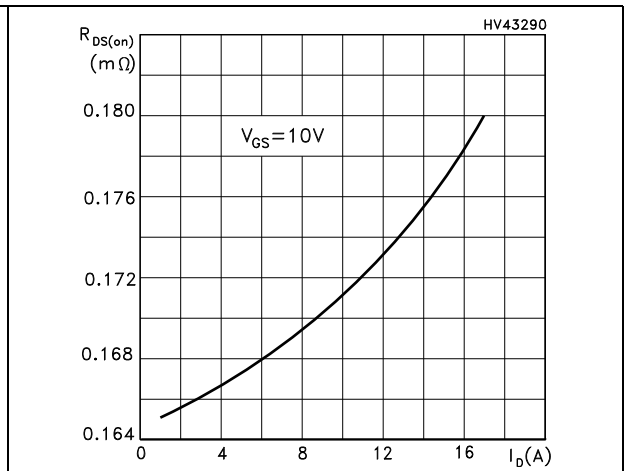


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations

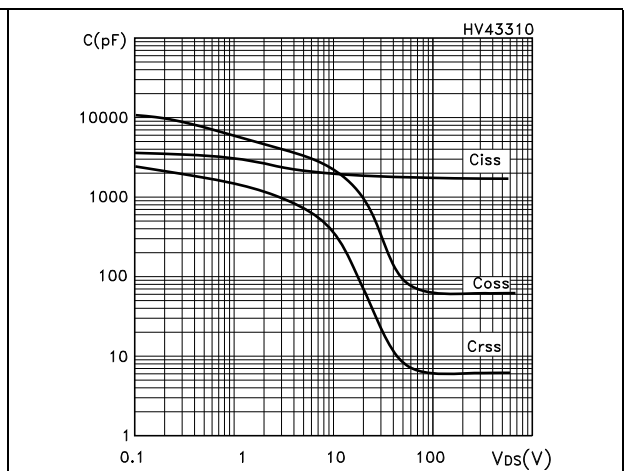
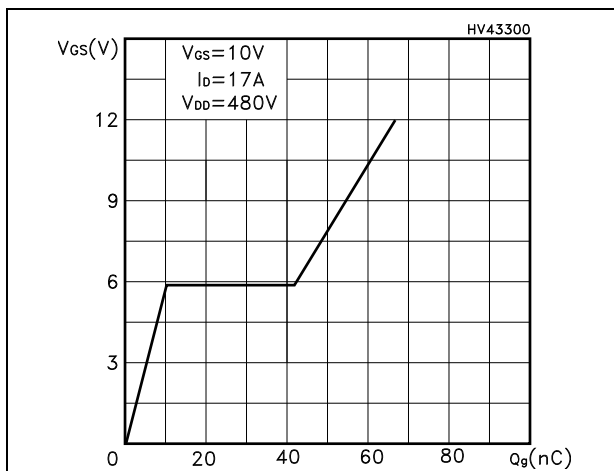


Figure 14. Normalized gate threshold voltage vs temperature

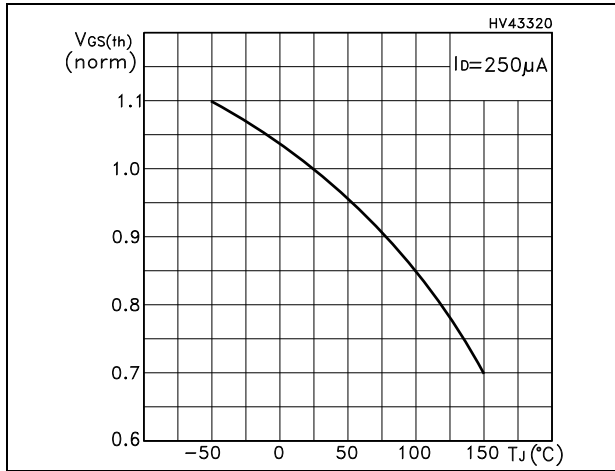


Figure 15. Normalized on-resistance vs temperature

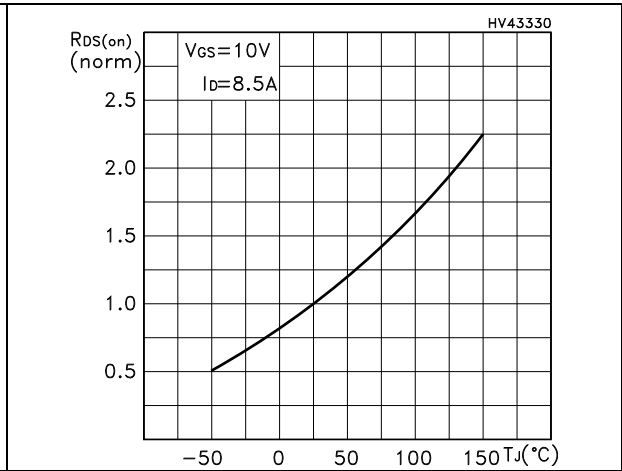


Figure 16. Source-drain diode forward characteristics

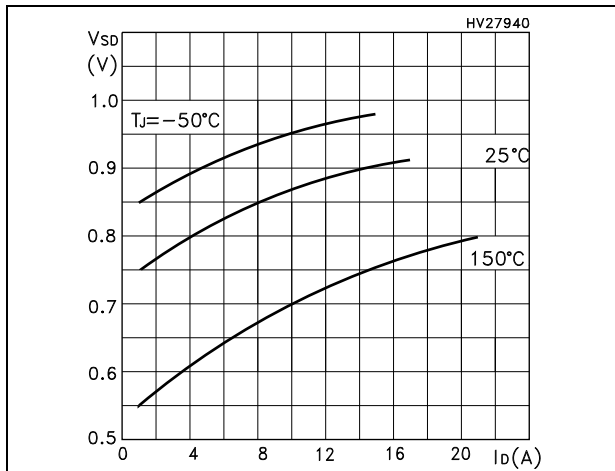
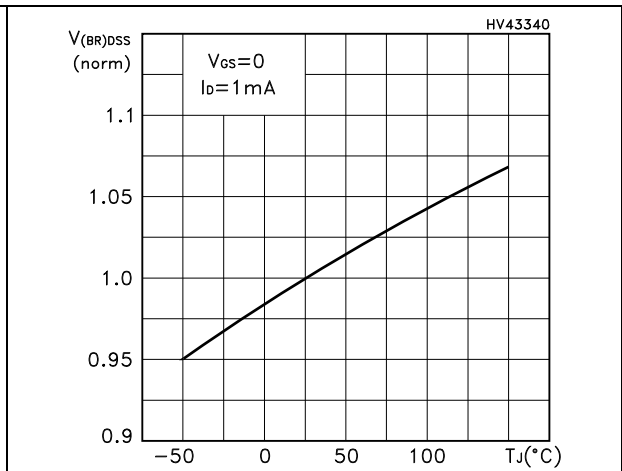
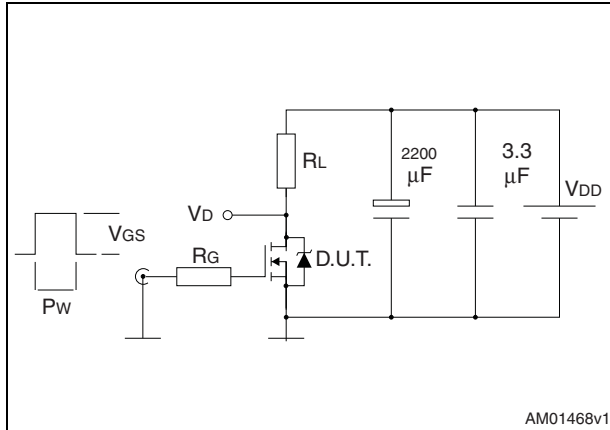


Figure 17. Normalized BV_{DSS} vs temperature



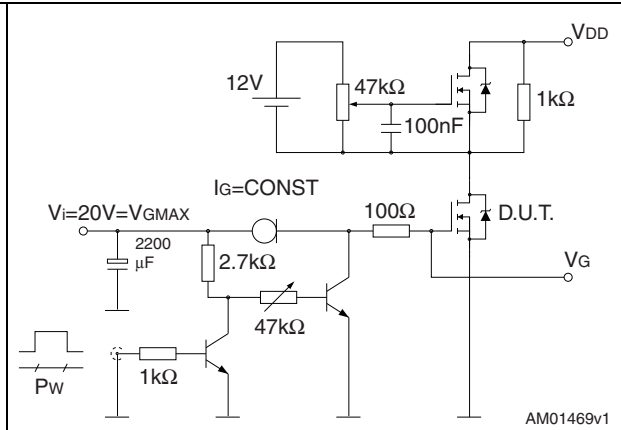
3 Test circuits

Figure 18. Switching times test circuit for resistive load



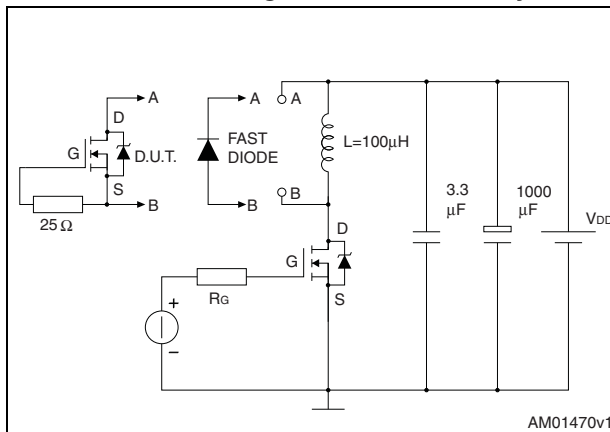
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Figure 19. Gate charge test circuit



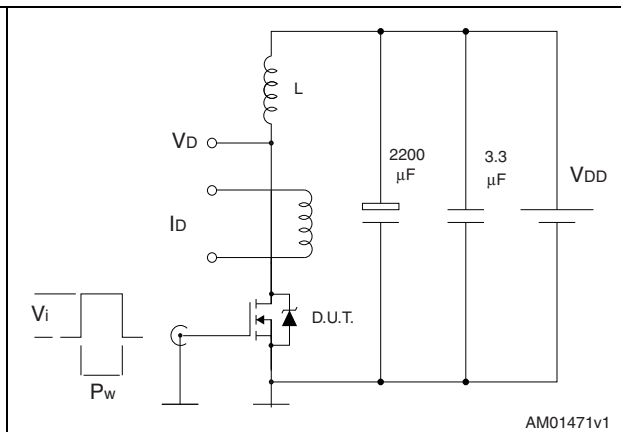
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Figure 20. Test circuit for inductive load switching and diode recovery times



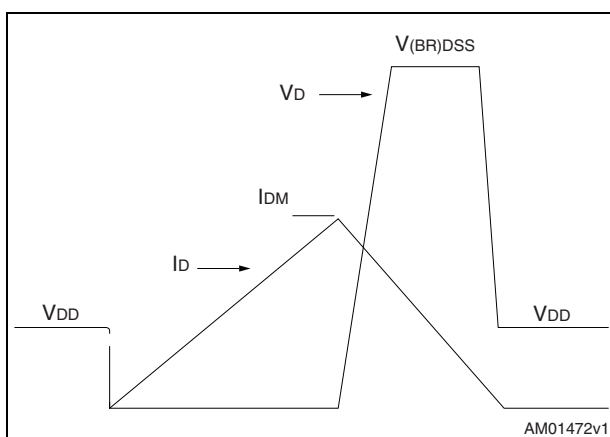
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Figure 21. Unclamped inductive load test circuit



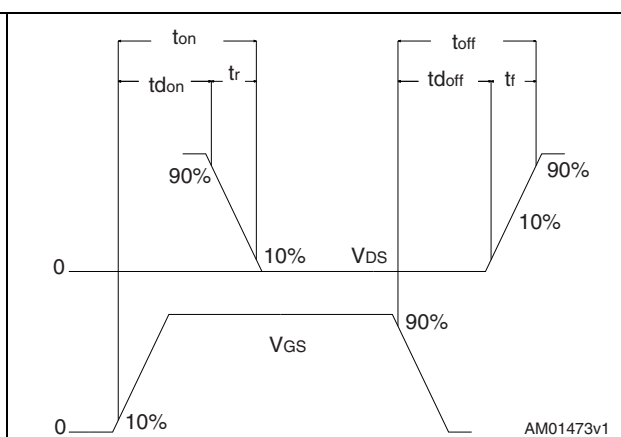
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Figure 22. Unclamped inductive waveform



AM01472v1

Figure 23. Switching time waveform



AM01473v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 24. D²PAK (TO-263) drawing

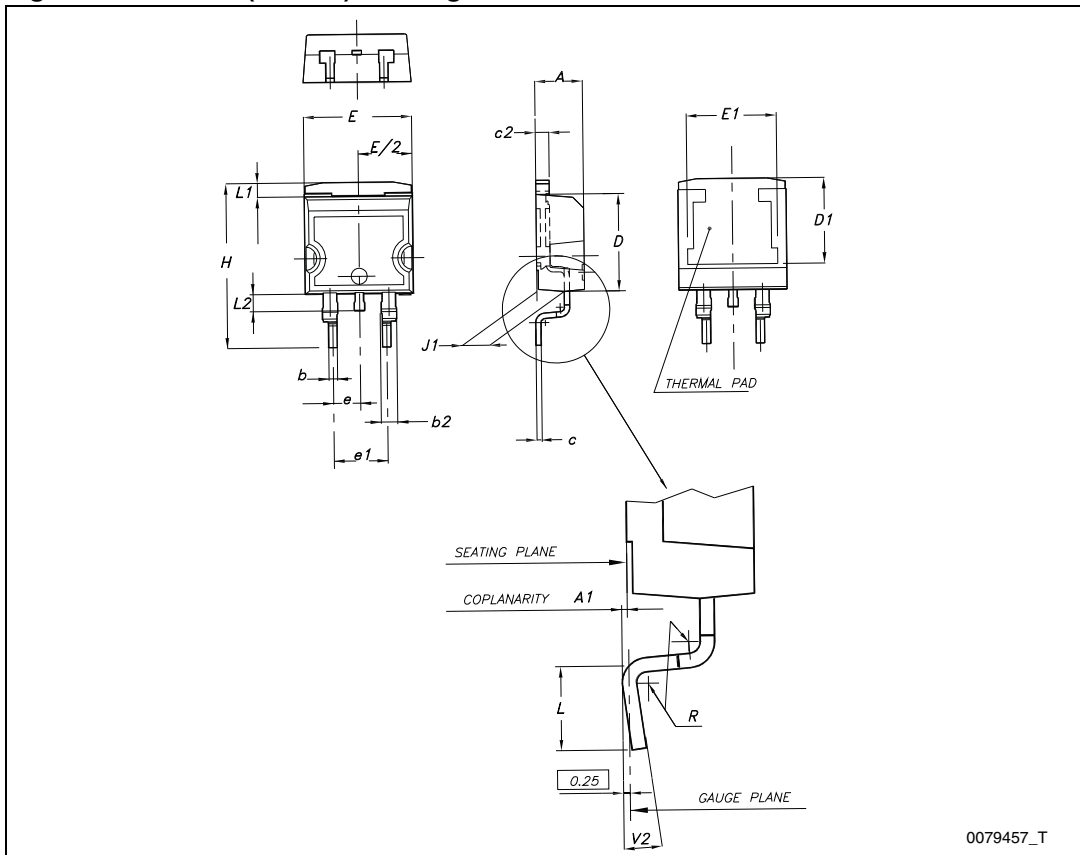
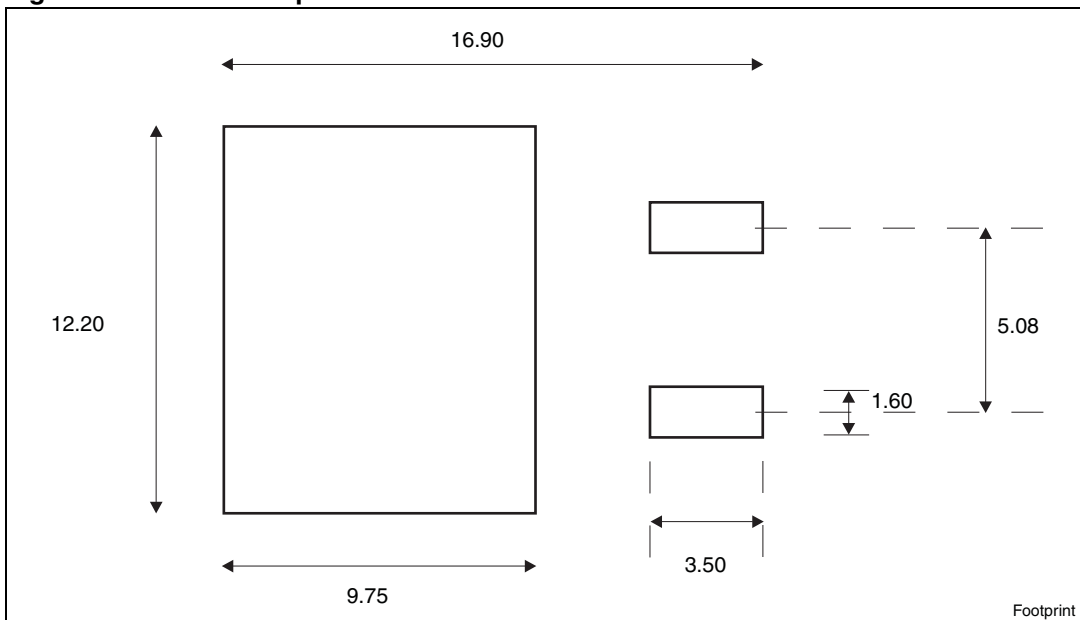


Figure 25. D²PAK footprint^(a)



a. All dimensions are in millimeters

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 26. TO-220FP drawing

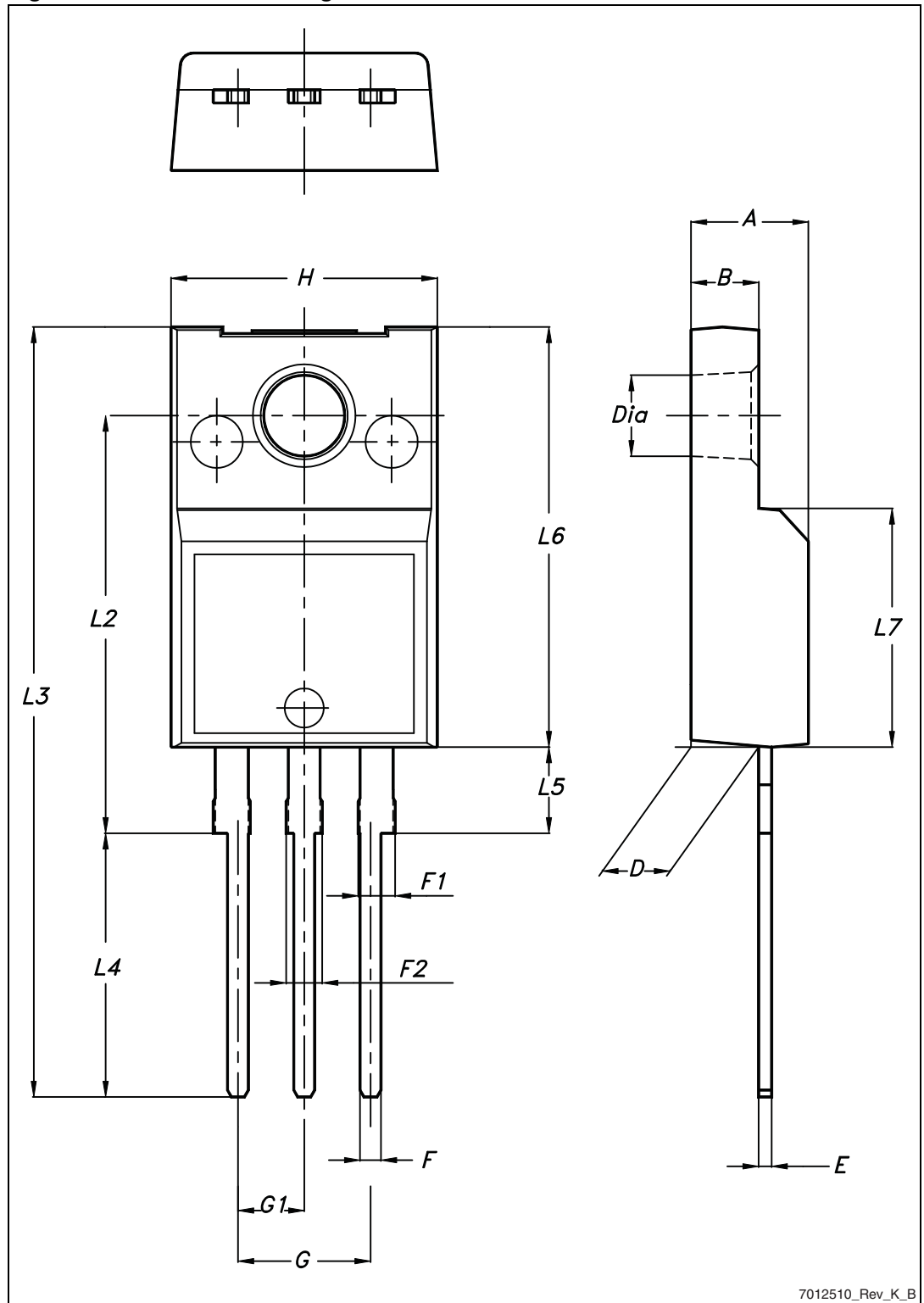


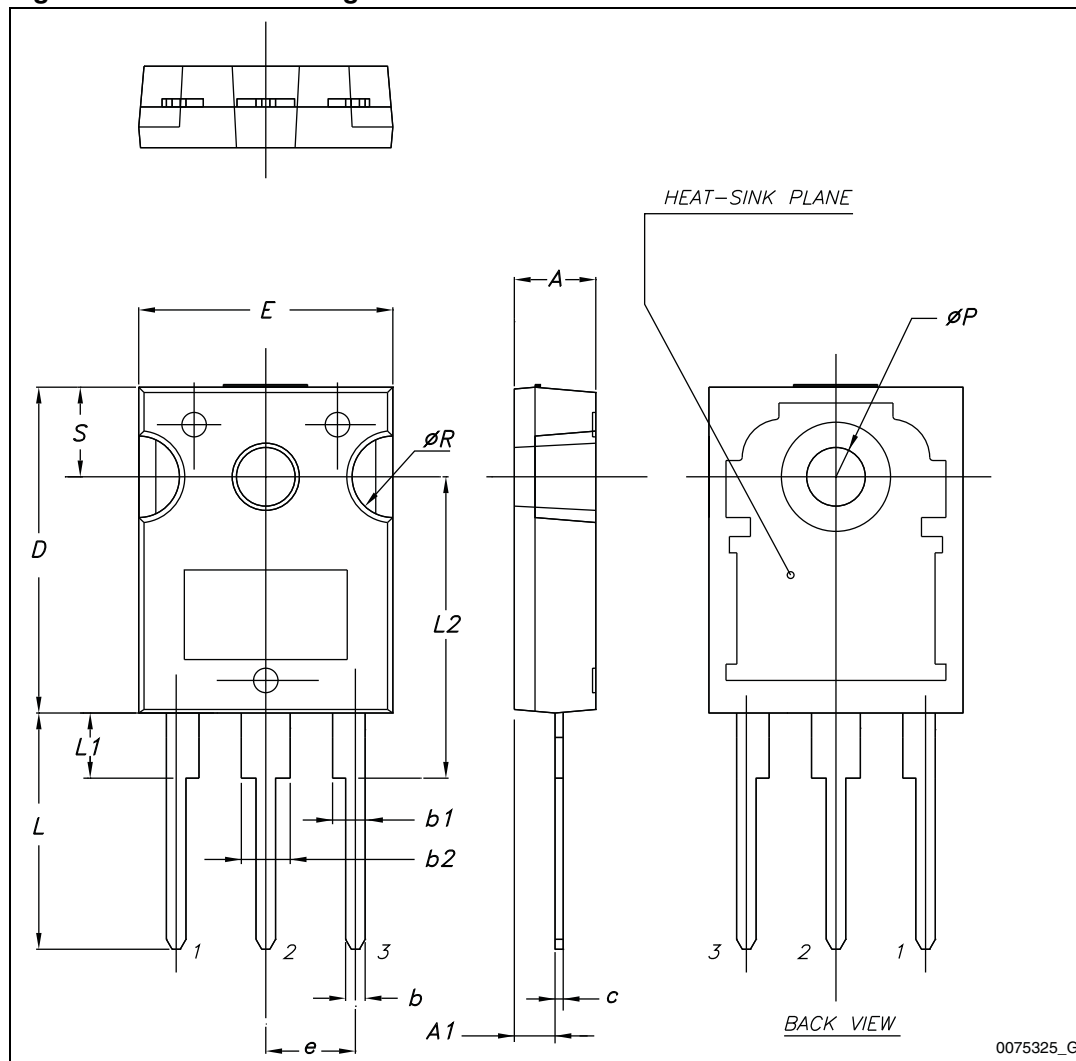
Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Table 11. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 28. TO-247 drawing



5 Packing mechanical data

Table 12. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 29. Tape

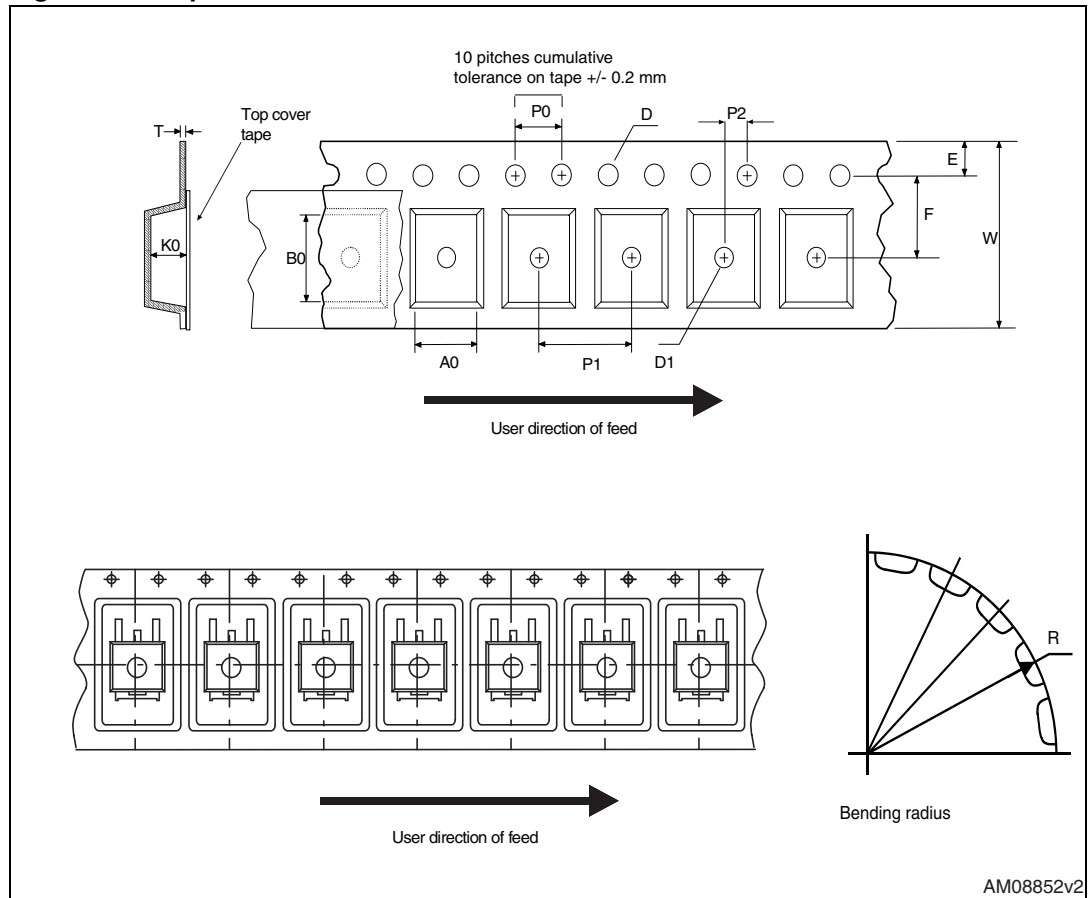
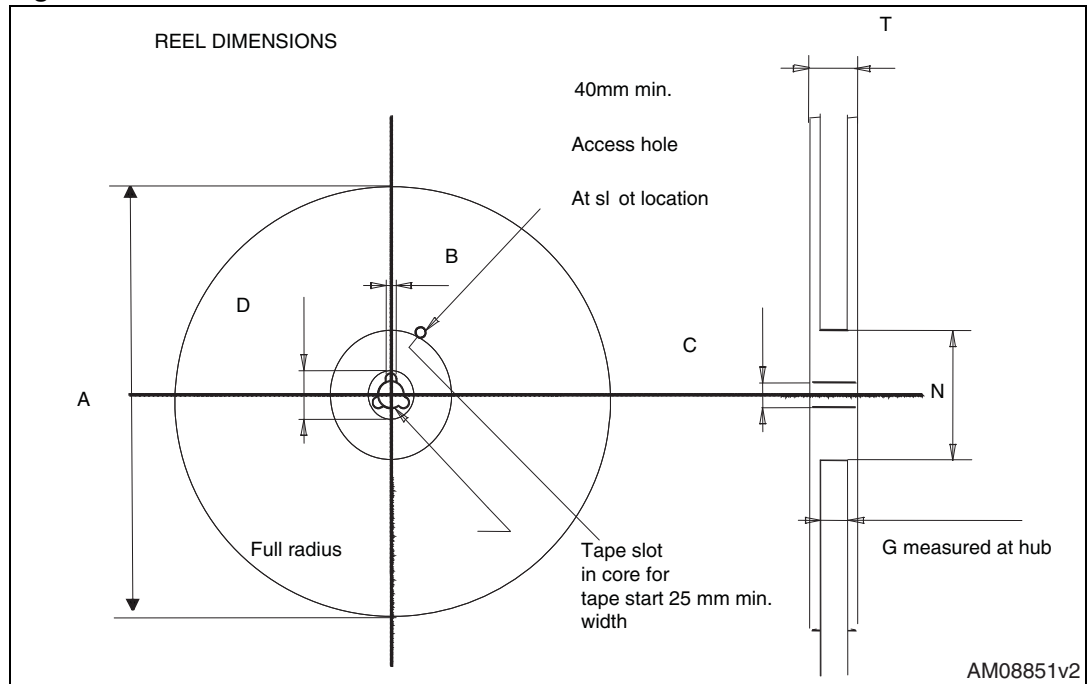


Figure 30. Reel



6 Revision history

Table 13. Document revision history

Date	Revision	Changes
05-Sep-2007	1	First release.
22-Apr-2008	2	Datasheet status promoted from preliminary data to datasheet.
27-Mar-2009	3	<i>Figure 13</i> has been updated. Updated ECOPACK [®] statement (<i>Section 4: Package mechanical data</i>)
16-Nov-2012	4	<i>Section 4: Package mechanical data</i> has been updated Minor text changes.

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